

## DOCUMENT CHANGE REQUEST

DCR number 1299 Changes required for: Qualification Originator: Steve Thacker

Date: 2020/02/06 Date sent: 2019/10/02 Organisation: ESCC Executive

Secretariat

Status: IMPLEMENTED

Title:	Diodes Microwave Silicon Schottky General Purpose, based on types BAS40 and BAS70		
Number:	5512/020	Issue:	5

Other documents affected:

5513/017-6, 5513/030-5

Page:

Various (See attached Mark-ups)

Paragraph:

Para 2.9 & various (See attached Mark-ups)

Original wording:

see original specs

Proposed wording:

Per request from Manufacturer Infineon, amend the Burn-in 2 conditions in line with their discussions with agency DLR, as follows for specifications:

: 5512/020 (was: PD = 240 +/-10 mW) : 5513/017 (was: IF = 90 +/-10 mA) : 5513/030 (was: PD = 490 +/-10 mW)

Change to be:

Para 2.9, Burn-in 2 Conditions

Amend table to now apply:

- Characteristic: Power Dissipation, PD,
- Test conditions: <= PD given in Para. 1.5 Maximum Ratings (mW)

(Note 1 still applies)

In addition, various other minor editorial changes are included (i.e. addition of internal paragraph references; corrected reference titles, corrected hyperlinks)

See attached spec mark-ups that detail all changes (highlighted yellow).

: 5512/020 draft 5

: 5513/017 draft 6

: 5513/030 draft 6

Justification:



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Attachments:

5512020\_draft\_5b\_for\_dcr.docx, 5513017\_draft\_6b\_for\_dcr.docx, 5513030\_draft\_6b\_for\_dcr.docx

Modifications:

Date signed:

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Approval signature:

N/A

2020-02-06